

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

### Product Summary



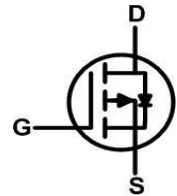
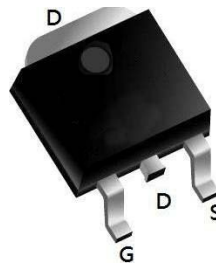
BVDSS	RDSON	ID
-30V	2.5mΩ	-120A

### Description

The XPX120P03FD is the high cell density P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XPX120P03FD meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### TO252-3L Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^{1,6}$	-120	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^{1,6}$	-80	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-470	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	580	mJ
$I_{AS}$	Avalanche Current	-80	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	100	W
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup> ( $t \leq 10S$ )	---	20	$^\circ\text{C/W}$
	Thermal Resistance Junction-ambient <sup>1</sup> (Steady State)	---	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-case <sup>1</sup>	---	3.6	$^\circ\text{C/W}$

**Table 3. Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

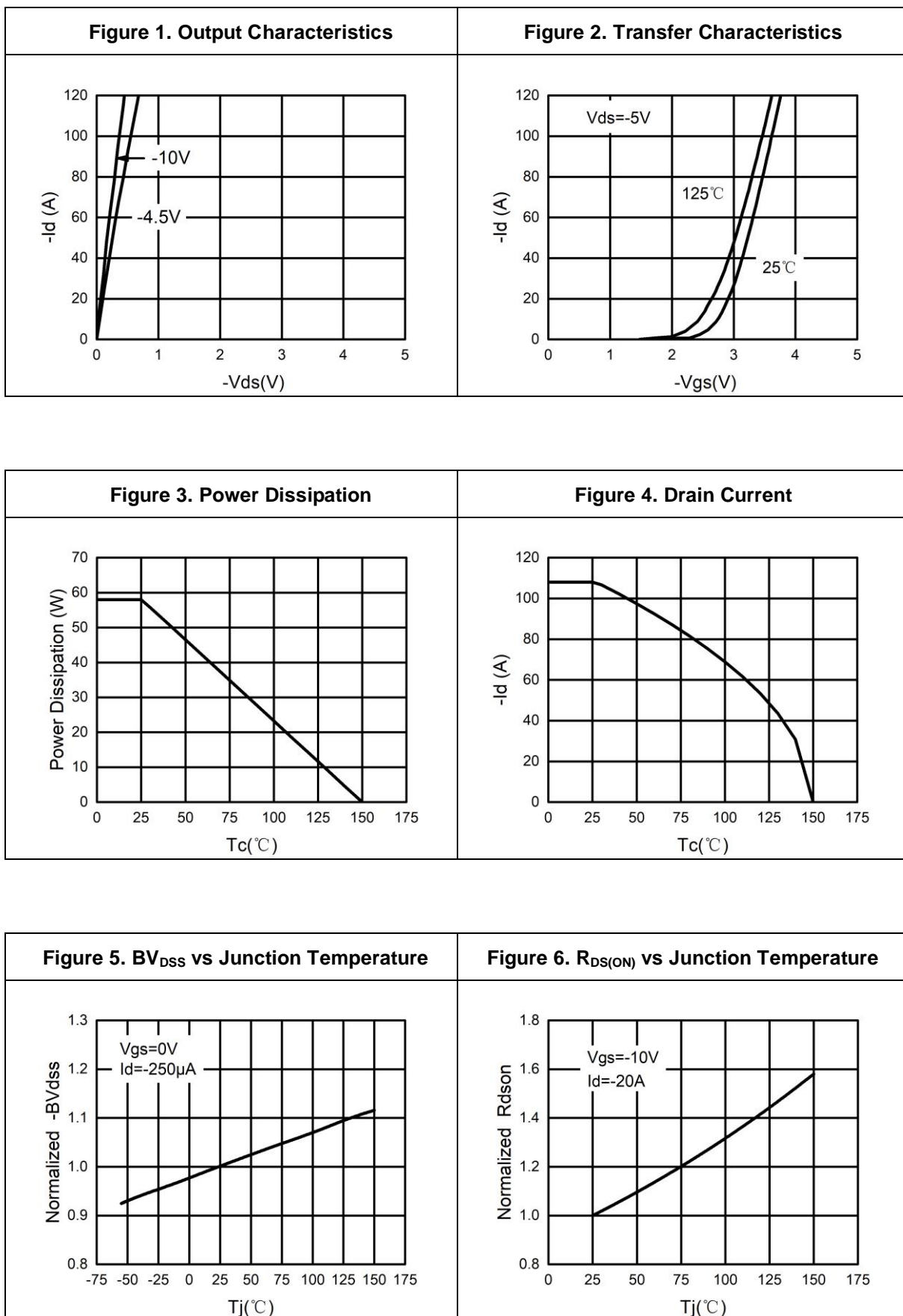
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.7	-2.5	V
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-20A		65		S
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A		2.5	3.1	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-20A		4	5.2	mΩ
Dynamic Characteristics						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHz		7000		pF
C <sub>oss</sub>	Output Capacitance			820		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			540		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1.0MHz		2.2		Ω
Switching Parameters						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =0.75Ω, R <sub>GEN</sub> =3Ω		14		nS
t <sub>r</sub>	Turn-on Rise Time			13		nS
t <sub>d(off)</sub>	Turn-Off Delay Time			65		nS
t <sub>f</sub>	Turn-Off Fall Time			37		nS
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-20A		130		nC
Q <sub>gs</sub>	Gate-Source Charge			12		nC
Q <sub>gd</sub>	Gate-Drain Charge			31		nC
Source-Drain Diode Characteristics						
I <sub>SD</sub>	Source-Drain Current (Body Diode)				-108	A
V <sub>SD</sub>	Forward on Voltage <sup>(Note 3)</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-20A			-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =-20A, di/dt=100A/μs		30		ns
Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> =-20A, di/dt=100A/μs		40		nC

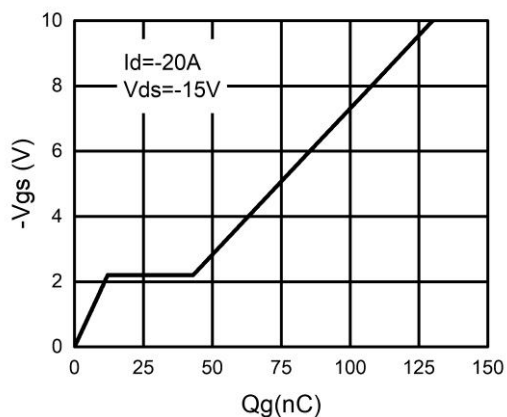
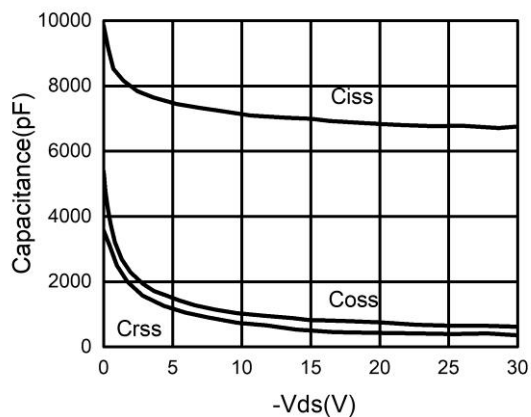
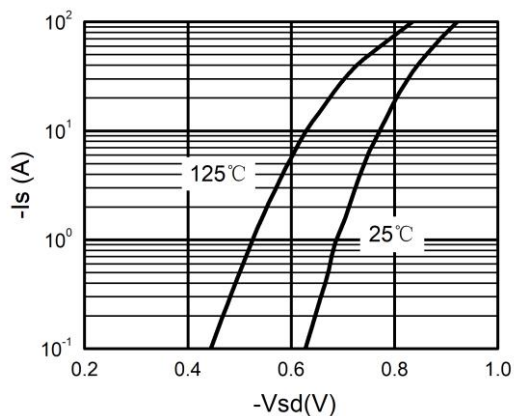
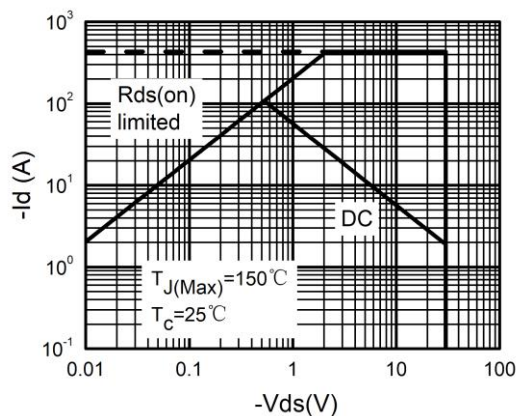
Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

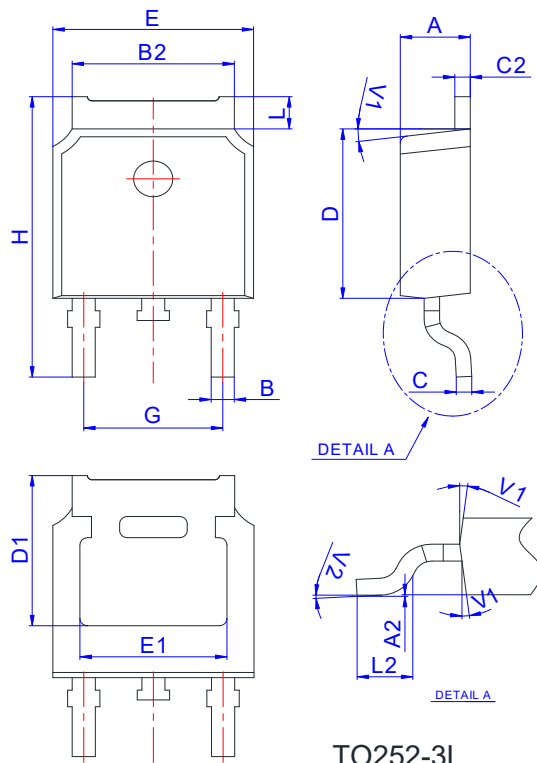
Notes 2.E<sub>AS</sub> condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=15V, V<sub>G</sub>=-10V, R<sub>g</sub>=25Ω, L=0.5mH.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

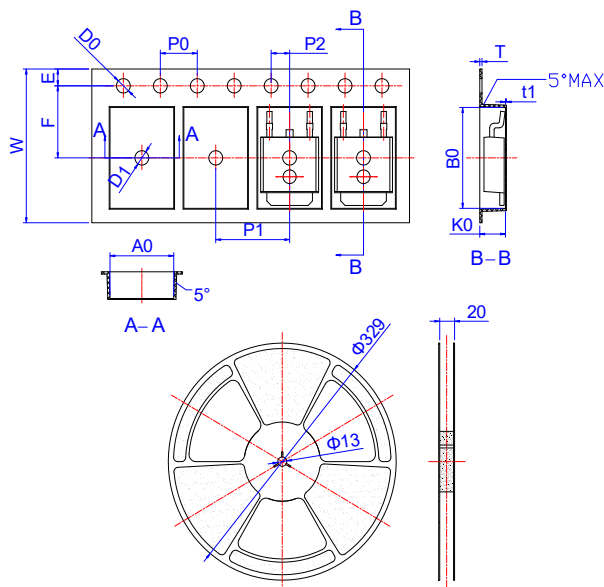
## Typical Electrical And Thermal Characteristics (Curves)



**Figure 7. Gate Charge Waveforms**

**Figure 8. Capacitance**

**Figure 9. Body-Diode Characteristics**

**Figure 10. Maximum Safe Operating Area**


**Package Mechanical Data-TO252-3L**


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

**Reel Spectification-TO252-3L**


Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C $\pm$ 5°C	5sec $\pm$ 1 sec
Pb-Free device	260°C $\pm$ 0/-5°C	5sec $\pm$ 1 sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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